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# N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)			
100	0.120 at V <sub>GS</sub> = 10 V	3.8			
100	0.155 at V <sub>GS</sub> = 4.5 V	3.2			

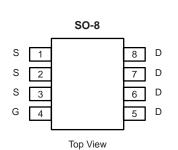
#### **FEATURES**

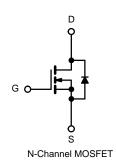
- DT-Trench Power MOSFET
- 175 °C Junction Temperature
- 100 % R<sub>g</sub> and UIS Tested



### **APPLICATIONS**

- Load Switch
- LED Backlighting in LCD TVs





<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)						
Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V <sub>DS</sub>	100	V		
Gate-Source Voltage		$V_{GS}$	± 20	V		
Continuous Drain Current (T <sub>.1</sub> = 175 °C) <sup>b</sup>	T <sub>C</sub> = 25 °C	I.	3.8			
Continuous Drain Current (1) = 175 °C)	T <sub>C</sub> = 70 °C	- ' <sub>D</sub> -	3.0			
Pulsed Drain Current		I <sub>DM</sub>	15	Α		
Continuous Source Current (Diode Conduction)	I <sub>S</sub>	3.8				
Avalanche Current	I <sub>AR</sub>	4.0				
Repetitive Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E <sub>AR</sub>	12	mJ		
Mayimum Dayyar Dissination	T <sub>C</sub> = 25 °C	P <sub>D</sub>	4.5 <sup>b</sup>	W		
Maximum Power Dissipation	T <sub>A</sub> = 25 °C	T D	2.3 <sup>a</sup>			
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
lunation to Ambianta	t ≤ 10 s	D	45	60		
Junction-to-Ambient <sup>a</sup>	Steady State	R <sub>thJA</sub>	20	30	°C/W	
Junction-to-Case		R <sub>thJC</sub>	2.5	5		

#### Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. See SOA curve for voltage derating.



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Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit	
Static	L				l l		
Drain-Source Breakdown Voltage	$V_{DS}$ $V_{GS} = 0 \text{ V, } I_D = 250 \mu\text{A}$ 100		100				
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1		3	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
	I <sub>DSS</sub>	V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V			1		
Zero Gate Voltage Drain Current		V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50 μA		
		V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			250	1	
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	3.8			Α	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2.7 A	0.120 0.12		0.127		
D : 0	D	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2.5 A, T <sub>J</sub> = 125 °C			0.139		
Drain-Source On-State Resistance <sup>b</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2.5 A, T <sub>J</sub> = 175 °C			0.144	Ω	
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 2.0 A		0.155	0.165		
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 2.7 A		7		S	
Dynamic <sup>a</sup>							
Input Capacitance	C <sub>iss</sub>			1880		pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 80 \text{ V}, f = 1 \text{ MHz}$		900			
Reverse Transfer Capacitance	C <sub>rss</sub>			75			
Total Gate Charge <sup>c</sup>	$Q_g$			4	8		
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	$V_{DS} = 80 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 2.7 \text{ A}$		1.6		nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			1.1			
Gate Resistance	R <sub>g</sub>			2		Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			8			
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 80 \text{ V}, R_L = 5 \Omega$		13	_	ne	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 2.7 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 2.5 \Omega$		10		ns	
Fall Time <sup>c</sup>	t <sub>f</sub>			14			
Source-Drain Diode Ratings and Cha	racteristic (T	C = 25 °C)		_			
Pulsed Current	I <sub>SM</sub>				15	Α	
Diode Forward Voltage <sup>b</sup>	$V_{SD}$	$I_F = 2A$ , $V_{GS} = 0 V$		0.8	1.2	V	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 2A, dI/dt = 100 A/μs		55	80	ns	

#### Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- c. Independent of operating temperature.

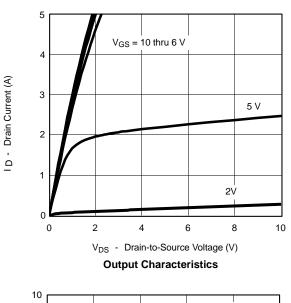
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

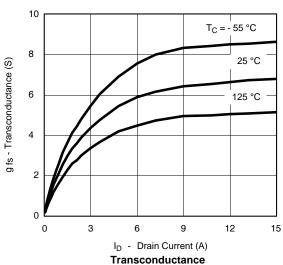


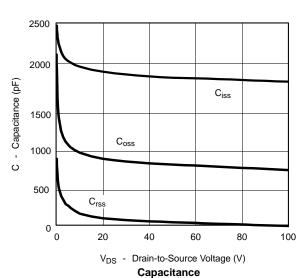


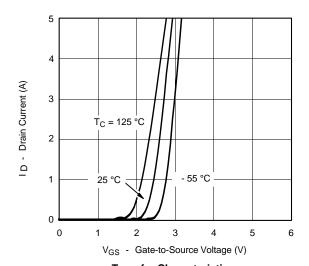
# TYPICAL CHARACTERISTICS (25 °C unless noted)

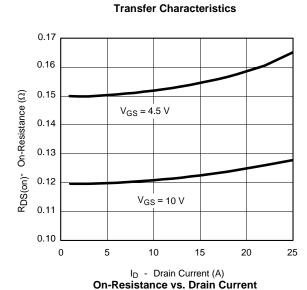


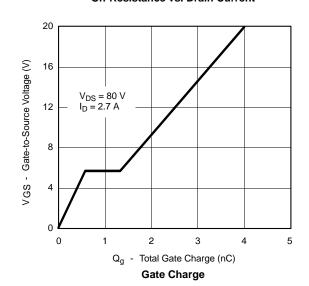








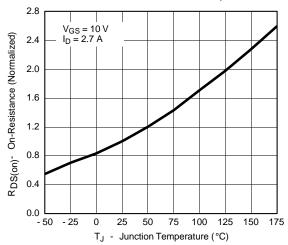






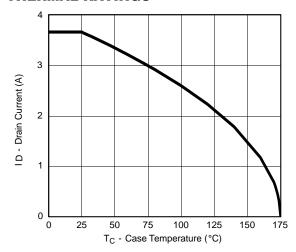


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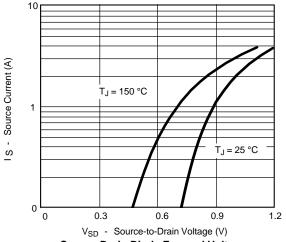


On-Resistance vs. Junction Temperature

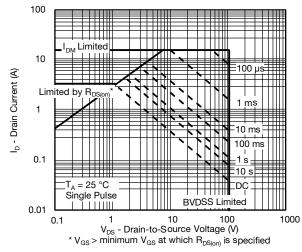
#### THERMAL RATINGS



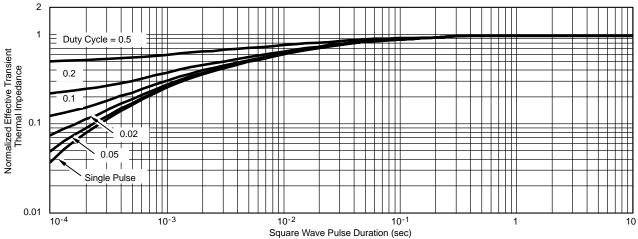
Maximum Avalanche Drain Current vs. Case Temperature



Source-Drain Diode Forward Voltage



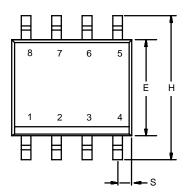
Safe Operating Area

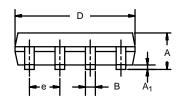


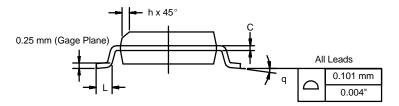
Normalized Thermal Transient Impedance, Junction-to-Case



**SOIC (NARROW): 8-LEAD** JEDEC Part Number: MS-012







	MILLIM	IETERS	INC	INCHES	
DIM	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A <sub>1</sub>	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.27 BSC		0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
FCN: C-06527-Rev I 11-Sen-06					

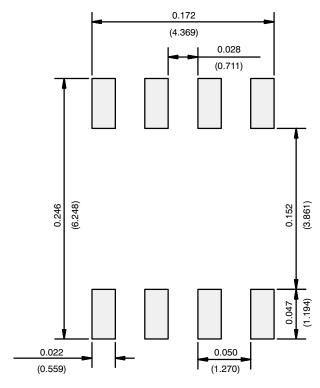
ECN: C-06527-Rev. I, 11-Sep-06

DWG: 5498

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#### **RECOMMENDED MINIMUM PADS FOR SO-8**



Recommended Minimum Pads Dimensions in Inches/(mm)

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